2SK3396

Silicon N-Channel Junction FET

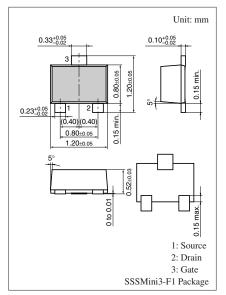
For impedance conversion in low frequency For infrared sensor

■ Features

- Low gate-source cutoff current I_{GSS}
- \bullet Small capacitance of short-circuit forward transfer capacitance (common source) C_{iss} , short-circuit output capacitance (common source) C_{oss} , reverse transfer capacitance (common source) C_{rss}

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Gate-drain voltage (Source open)	V_{GDO}	-40	V	
Gate-source voltage (Drain open)	V_{GSO}	-40	V	
Gate current	I_G	10	mA	
Drain current	I_{D}	1	mA	
Power dissipation	P_{D}	100	mW	
Channel temperature	T _{ch}	125	°C	
Storage temperature	T_{stg}	-55 to +125	°C	

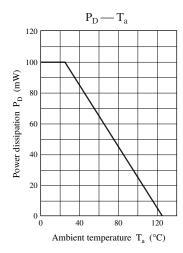


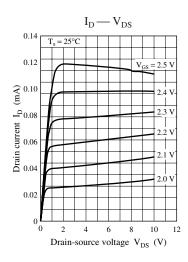
Marking Symbol: EB

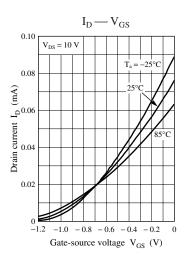
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

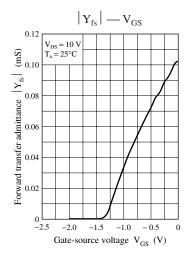
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Gate-drain surrender voltage	V_{GDS}	$I_G = -10 \mu\text{A}, V_{DS} = 0$	-40			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 10 \text{ V}, V_{GS} = 0$	30		200	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = -20 \text{ V}, V_{DS} = 0$			- 0.5	nA
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	0.05			mS
Gate-source cutoff voltage	V _{GSC}	$V_{DS} = 10 \text{ V}, I_D = 1 \mu A$		-1.3	-3.0	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		1.0		pF
Short-circuit output capacitance (Common source)	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		0.4		pF
Reverse transfer capacitance (Common source)	C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		0.4		pF

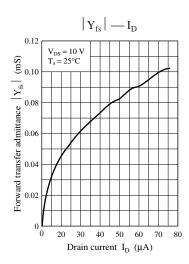
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.











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